

Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	60	V
Drain-Gate Voltage R _{GS} ≤ 1.0MΩ			V _{DGR}	60	V
Gate-Source Voltage Continuous Pulsed			V _{GSS}	±20 ±40	V
Continuous Drain Current (Note 5) V_{GS} = 10V	Steady State	T _A = +25°C T _A = +85°C T _A = +100°C	ID	170 120 105	mA
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T _A = +25°C T _A = +85°C T _A = +100°C	ID	210 150 135	mA
Maximum Continuous Body Diode Forward Current (Note 6) Continuous Pulsed			IS	0.2 0.5	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	800	mA

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Power Dissipation	(Note 5)	D	370	mW	
	(Note 6)	PD	540		
Thermal Resistance, Junction to Ambient	(Note 5)	D	348		
	(Note 6)	R _{0JA}	241	°C/W	
Thermal Resistance, Junction to Case	(Note 6)	R _{0JC}	91		
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C	

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

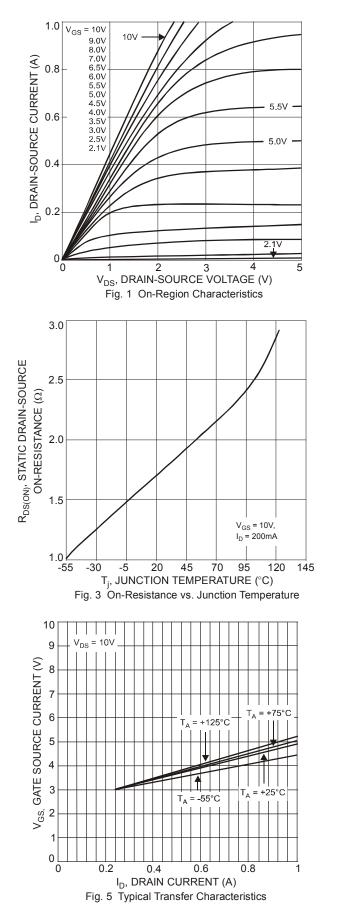
Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)				, ,,,				
Drain-Source Breakdown Voltage		BV _{DSS}	60	70		V	V _{GS} = 0V, I _D = 10µA	
Zero Gate Voltage Drain Current	@ T _J = +25°C @ T _J = +125°C	I _{DSS}		—	1.0 500	μA	V _{DS} = 60V, V _{GS} = 0V	
Gate-Body Leakage		IGSS	_	_	±10	nA	V_{GS} = ±20V, V_{DS} = 0V	
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage		V _{GS(TH)}	1.0	—	2.5	V	V_{DS} = V_{GS} , I_D = 250 μ A	
Static Drain-Source On-Resistance	@ T _J = +25°C @ T _J = +25°C @ T _J = +125°C	R _{DS(ON)}	_	3.2 2.4 4.4	7.5 5.0 13.5	Ω	$\label{eq:VGS} \begin{split} &V_{GS} = 5.0V, \ I_D = 0.05A \\ &V_{GS} = 10V, \ I_D = 0.5A \\ &V_{GS} = 10V, \ I_D = 0.5A \end{split}$	
On-State Drain Current		I _{D(ON)}	0.5	1.0		Α	V _{GS} = 10V, V _{DS} = 7.5V	
Forward Transconductance		g fs	80	_	_	mS	V _{DS} =10V, I _D = 0.2A	
Diode Forward Voltage		V _{SD}	_	0.78	1.5	V	V _{GS} = 0V, I _S = 115mA	
DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance		Ciss		22	50	pF		
Output Capacitance		Coss		11	25	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz	
Reverse Transfer Capacitance		Crss		2.0	5.0	pF		
Gate Resistance		Rg	_	120	_	Ω	$V_{DS} = 0V, V_{GS} = 0V,$ f = 1.0MHz	
Total Gate Charge (V _{GS} = 4.5V)		Qg	_	223	_			
Gate-Source Charge		Q _{gs}		82	_	рС	V _{DS} = 10V, I _D = 250mA	
Gate-Drain Charge		Q _{gd}		178	_			
Turn-On Delay Time		t _{D(ON)}	_	2.8			$V_{DD} = 30V, I_D = 0.2A,$ $R_L = 150\Omega, V_{GEN} = 10V,$	
Turn-On Rise Time		t _R		3.0				
Turn-Off Delay Time		t _{D(OFF)}	_	7.6		ns		
Turn-Off Fall Time		t _F	_	5.6]	R _{GEN} = 25Ω	

Notes:

Device mounted on FR-4 PCB, with minimum recommended pad layout.
Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.





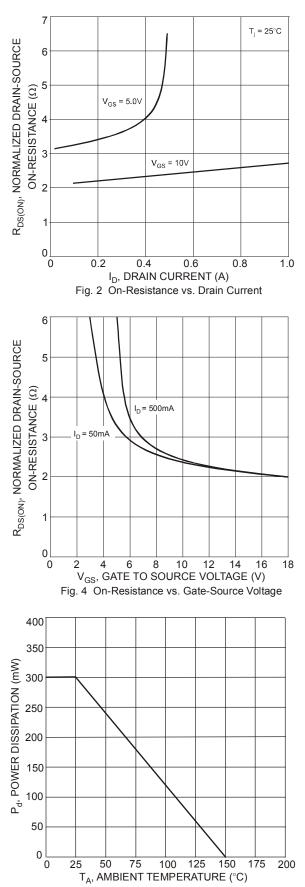
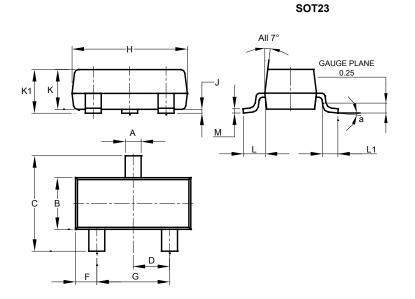


Fig. 6 Max Power Dissipation vs. Ambient Temperature



Package Outline Dimensions

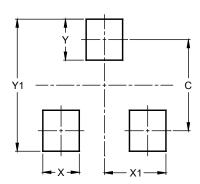
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	SOT23						
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All	All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23

Dimensions	Value (in mm)		
С	2.0		
Х	0.8		
X1	1.35		
Y	0.9		
Y1	2.9		

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